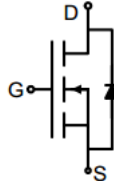



N-Channel Enhancement Mode Power MOSFET

Description <p>The GT130N03D5 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.</p>		 <p>Schematic Diagram</p>  <p>DFN5X6-8L</p>	
General Features <ul style="list-style-type: none"> ● V_{DS} 30V ● I_D (at $V_{GS} = 10V$) 115A ● $R_{DS(ON)}$ (at $V_{GS} = 10V$) < 3.5mΩ ● $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) < 6mΩ ● 100% Avalanche Tested ● RoHS Compliant 			
Application <ul style="list-style-type: none"> ● Synchronous Rectification in SMPS or LED Driver ● UPS ● Motor Control ● BMS ● High Frequency Circuit 			
Device	Package	Marking	Packaging
GT130N03D5	DFN5X6-8L	GT130N03	2500pcs/Reel

Absolute Maximum Ratings $T_C = 25^\circ C$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Continuous Drain Current	I_D	115	A
Pulsed Drain Current (note1)	I_{DM}	345	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	P_D	36	W
Single pulse avalanche energy (note3)	E_{AS}	156	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^\circ C$

Thermal Resistance

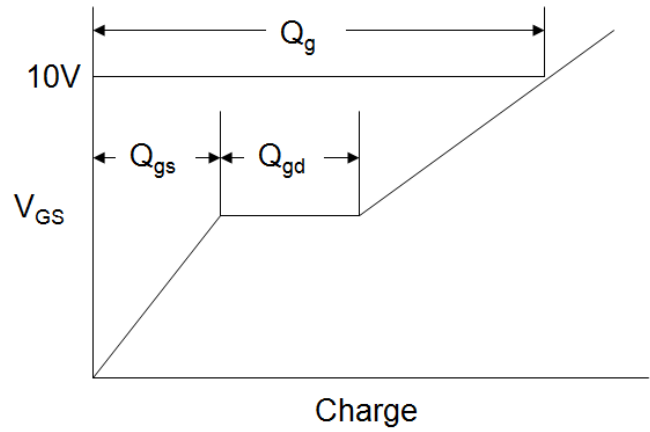
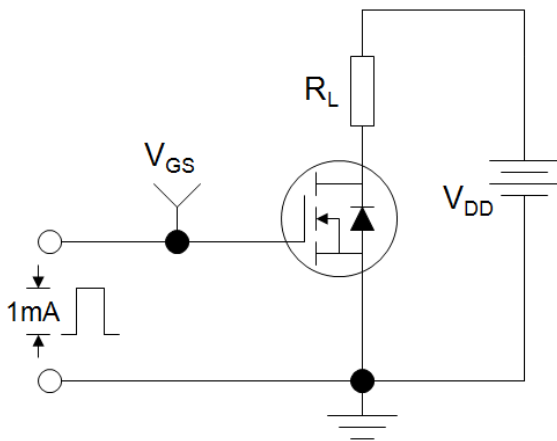
Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	40	$^\circ C/W$
Thermal Resistance, Junction-to-Case	R_{thJC}	2.8	$^\circ C/W$

Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0V$	--	--	1	μA
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.5	2.2	V
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 50A$	--	2.5	3.5	m Ω
		$V_{GS} = 10V, I_D = 10A$	--	2.5	3.5	
		$V_{GS} = 4.5V, I_D = 50A$	--	3.5	6	
		$V_{GS} = 4.5V, I_D = 10A$	--	3.5	6	
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 15V,$ $f = 1.0MHz$	--	1330	--	pF
Output Capacitance	C_{oss}		--	360	--	
Reverse Transfer Capacitance	C_{rss}		--	55	--	
Total Gate Charge	Q_g	$V_{DS} = 15V,$ $I_D = 20A,$ $V_{GS} = 10V$	--	20	--	nC
Gate-Source Charge	Q_{gs}		--	3.5	--	
Gate-Drain Charge	Q_{gd}		--	3.5	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DS} = 15V,$ $I_D = 20A,$ $R_G = 3\Omega$	--	8	--	ns
Turn-on Rise Time	t_r		--	3	--	
Turn-off Delay Time	$t_{d(off)}$		--	20	--	
Turn-off Fall Time	t_f		--	3	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	40	A
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_S = 1A, V_{GS} = 0V$	--	--	1.2	V

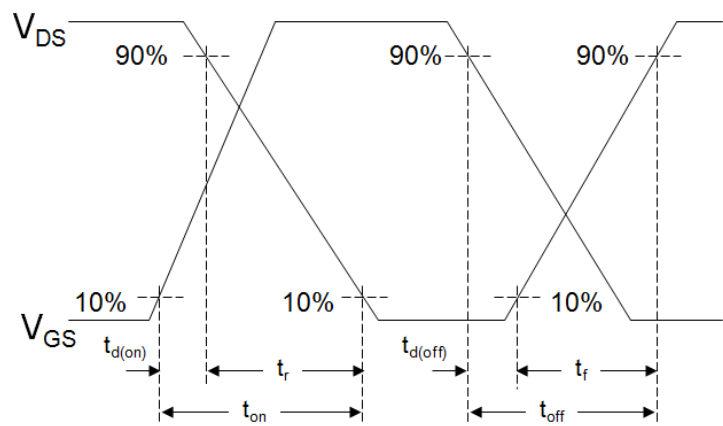
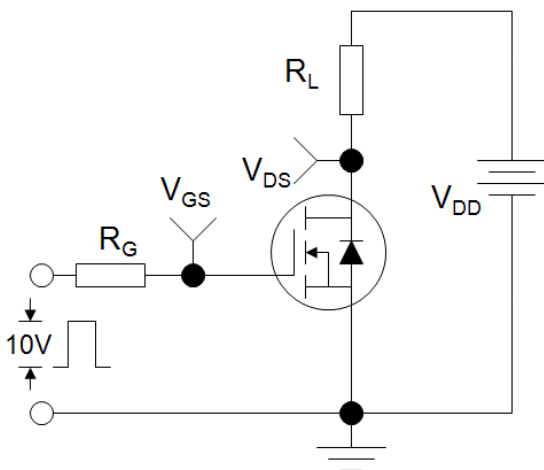
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. Identical low side and high side switch with identical R_G
3. EAS condition : $T_J = 25^\circ\text{C}, V_{DD} = 30V, V_{GS} = 10V, L = 0.5mH, R_g = 25\Omega$

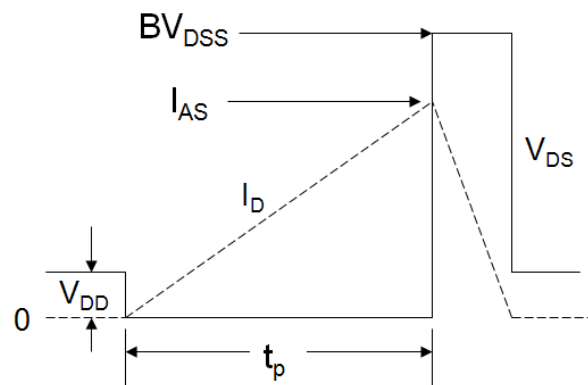
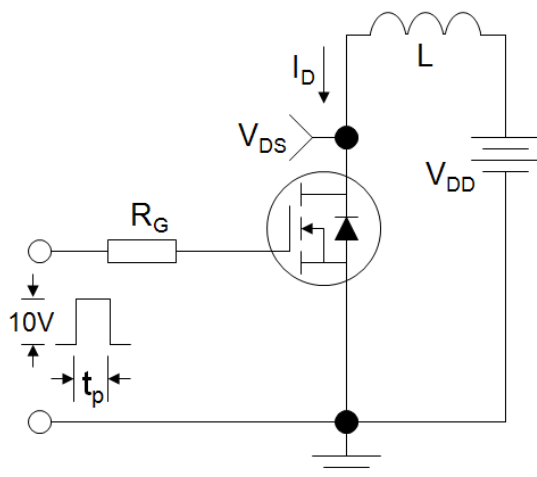
Gate Charge Test Circuit



EAS Test Circuit



Switch Time Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

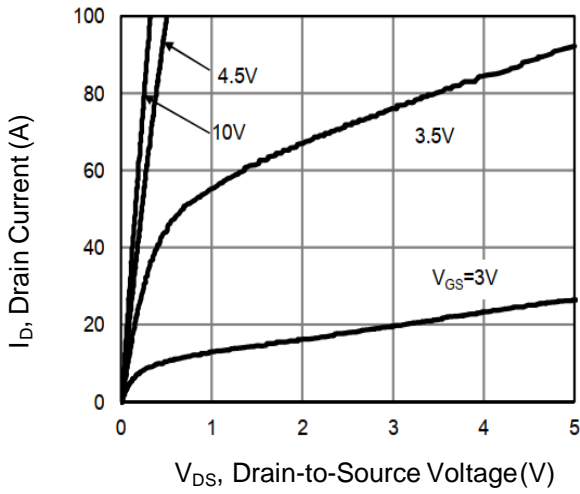


Figure 2. Transfer Characteristics

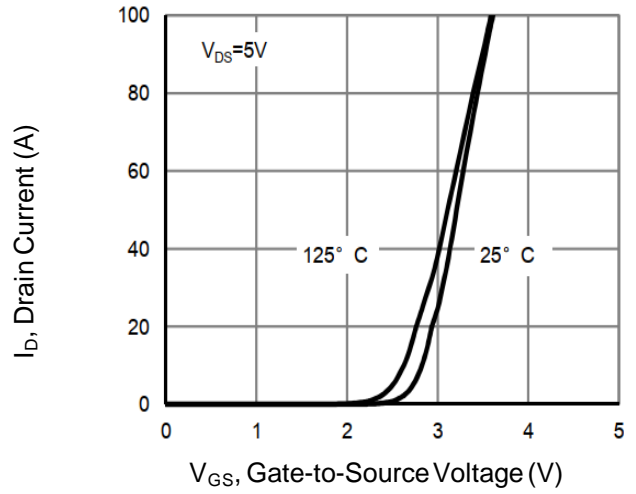


Figure 3. $R_{DS(on)}$ -Drain Current

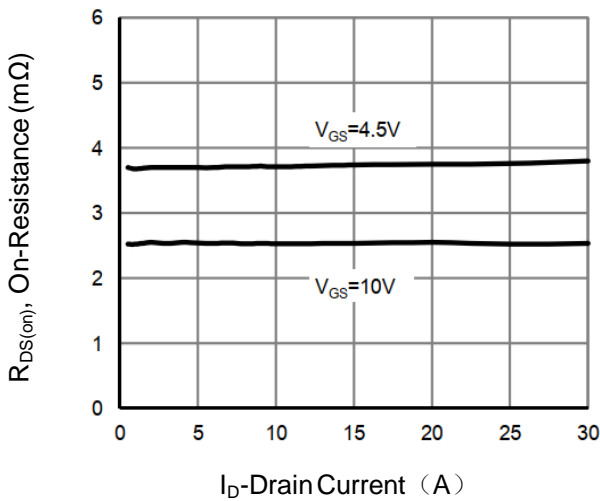


Figure 4. Gate Charge

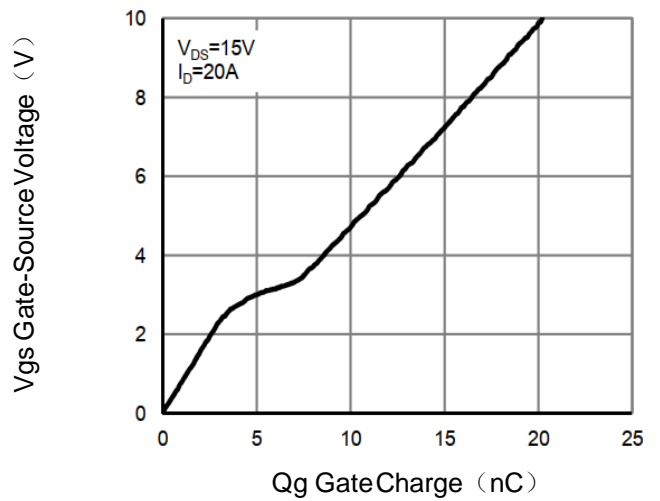


Figure 5. Capacitance vs Vds

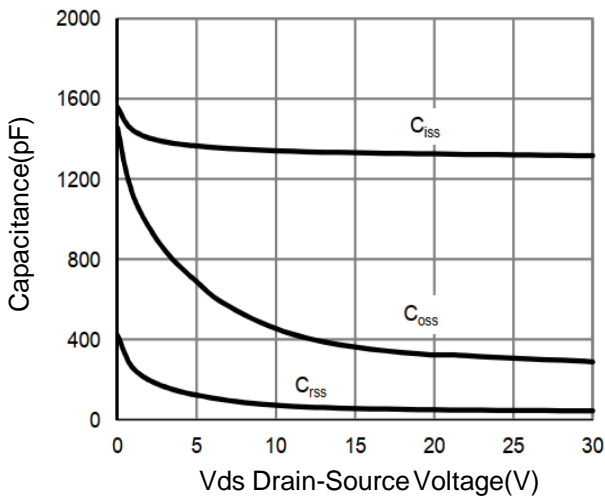
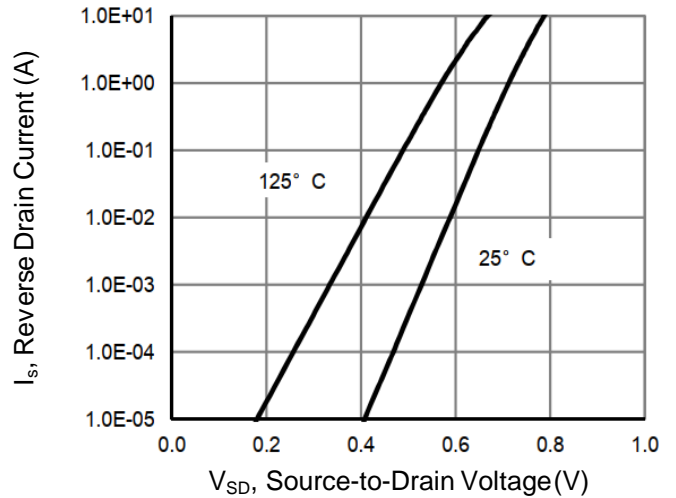


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

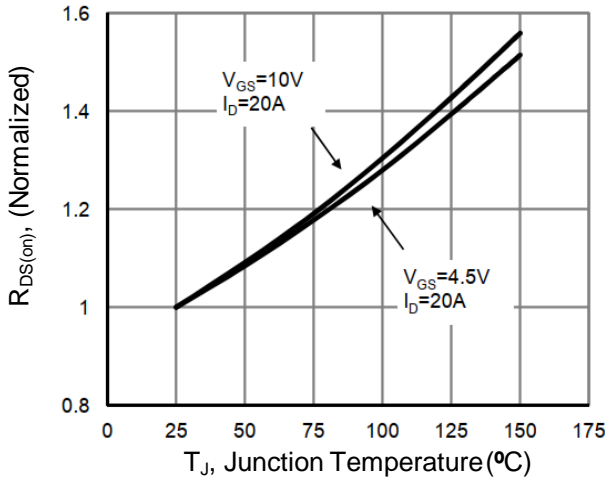


Figure 8. On-Resistance vs. Gate-Source Voltage

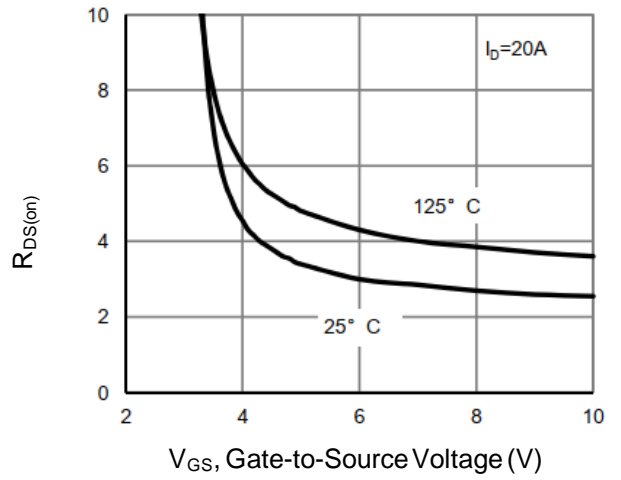


Figure 9. Normalized Maximum Transient Thermal Impedance

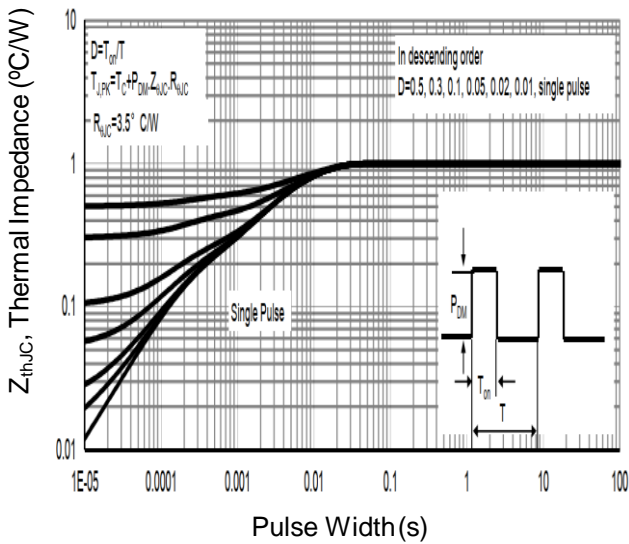
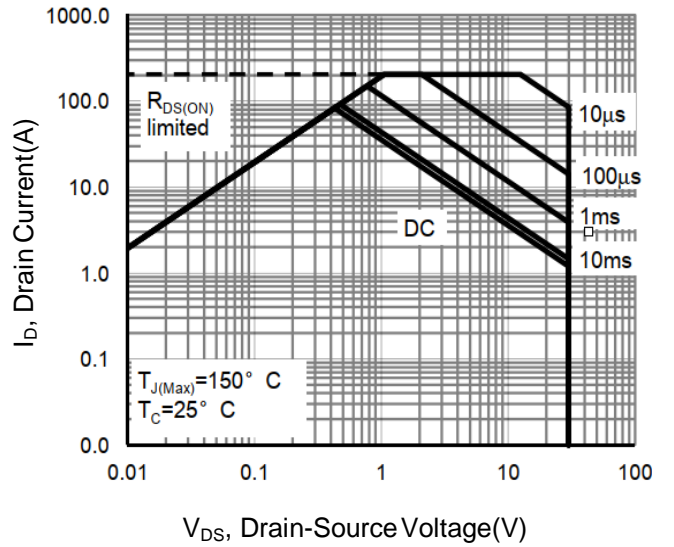
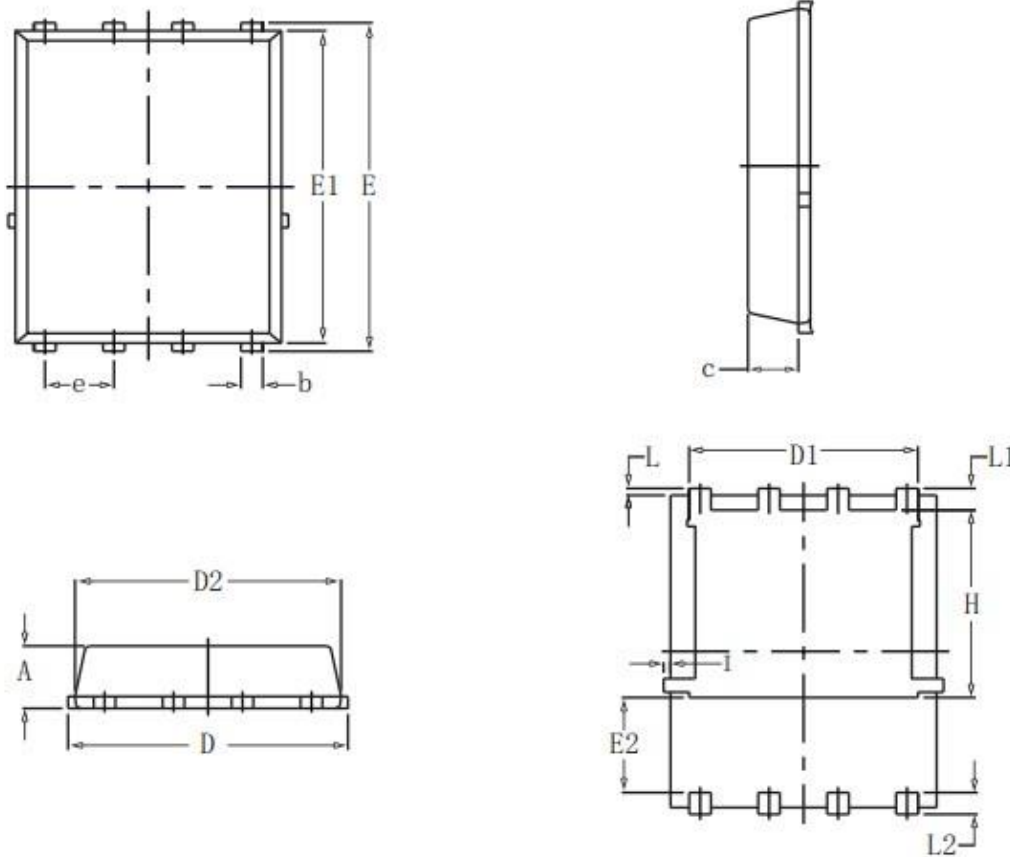


Figure 10. Safe Operation Area



DFN5~~X~~ -8L Package Information



SYMBOL	COMMON			
	MM		INCH	
	MIN	MAX	MIN	MAX
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.970	0.0324	0.0382
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.59	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	-	0.0630	-
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	-	0.18	-	0.0070